## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Makoto IIDA et al.

New U.S. National Phase of PCT/JP2005/000839

Filed: July 25, 2006 Docket No.: 128832

For: A SILICON SINGLE CRYSTAL, A SILICON WAFER, AN APPARATUS FOR PRODUCING THE SAME, AND A METHOD FOR PRODUCING THE SAME

## INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

Pursuant to 37 CFR §1.56, the attention of the Patent and Trademark Office is hereby directed to the references listed on the attached PTO-1449. Unless otherwise indicated herein, one copy of each reference is attached. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the references be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

- 1. This Information Disclosure Statement is being filed (a) within three months of the U.S. filing date of this non-CPA application, OR (b) before the mailing date of a first Office Action on the merits in the present application. No certification or fee is required.
- 2. Relevance of one or more non-English language reference is discussed in the present specification. See References 12-15.
- 3. One or more reference cited herein was cited in the International Search Report. An English language version of the International Search Report is attached for the Examiner's information. See References 3-11.
- 4. In accordance with 37 CFR §1.98(a)(2)(ii), copies of any U.S. patents and patent application publications are not attached.
- 5. An English language Abstract of one or more non-English language reference is attached hereto. See References 3-15.
- 6. A computer-generated English language translation of one or more Japanese Patent Publication cited herein has been obtained from the website of the Japanese Patent Office ([http://www.jpo.go.jp]), and is attached, but has not been reviewed for accuracy. See References 4-6 and 9-15.

## 10/586953

## New U.S. National Phase of PCT/JP2005/000839 IAP11 Rec'd PCT/PTO 25 JUL 2006

7. References <u>1 and 2</u> correspond to references <u>3 and 9</u>, respectively.

Respectfully submitted,

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WPB:JOC/jdb

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Date: July 25, 2006

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ATTY DOCKET NO. Form PTO-1449 US Dept. of Commerce Phase of (REV. 1/06) PATENT & TRADEMARK OFFICE 128832 PCT/JP2005/000839 INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary) **APPLICANTS** Makoto IIDA et al. FILING DATE July 25, 2006 U.S. PATENT DOCUMENTS Cite Examiner Initials No. Document Number Date Name 11/26/1991 Yokota et al. 1 5,067,989 3/11/1997 2 5,609,682 Sato et al. FOREIGN PATENT DOCUMENTS With With Examiner Cite Initials No. Document Number Date Country English English Abstract Translation 3 JP A 03-080193 4/4/1991 Japan Х 4/27/1999 Х Х 4 JP A 11-116392 Japan JP A 2000-327493 11/28/2000 Х Х 5 Japan 6 JP A 06-234597 8/23/1994 Japan Х Х WIPO Х 7 WO 01/81661 A1 11/1/2001 JP A 04-108683 4/9/1992 х 8 Japan X  $\mathbf{x}$ 9 JP A 08-073293 3/19/1996 Japan 10 JP A 06-340491 12/13/1994 Japan Х Х х Х 8/26/1997 11 JP A 09-221381 Japan X Х 1/25/1994 12 JP A 06-016495 Japan 12/24/1996 Х X 13 JP A 08-337493 Japan 14 JP A 10-007488 1/13/1998 Japan Х Х х Х 3/8/2002 15 JP A 2002-068886 Japan OTHER DOCUMENTS Examiner Cite (Including Author, Title, Date, Pertinent Pages, etc.) Initials No. Istratov et al.; "Physics of Copper in Silicon;" Journal of the Electrochemical Society Vol. 149, pp. G21-G30, 2002 16 DATE CONSIDERED **EXAMINER** Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance Examiner: and not considered. Include copy of this form with next communication to applicant.

Date: July 25, 2006